



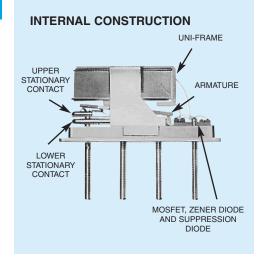
A Unit of Teledyne Electronics and Communications

CENTIGRID® ESTABLISHED RELIABILITY RELAY DPDT

SENSITIVE CMOS COMPATIBLE

SERIES 136C

SERIES DESIGNATION	RELAY TYPE			
136C	DPDT sensitive relay with internal power MOSFET driver, Zener diode gate protection, and diode coil suppression			



DESCRIPTION

The sensitive 136C Centigrid® relay is an ultraminiature, hermetically sealed, armature relay capable of being directly driven by most IC logic families. Its low profile height and .100" grid spaced terminals, which precludes the need for spreader pads, make it ideal for applications where extreme packaging density and/or close PC board spacing are required.

The basic concept and internal mechanical structure are similar to the 114 DPDT relay. The following unique construction features and manufacturing techniques provide overall high reliability and excellent resistance to environmental extremes:

- All welded construction.
- Unique uni-frame design providing high magnetic efficiency and mechanical rigidity.
- High force/mass ratios for resistance to shock and vibration.
- Advanced cleaning techniques provide maximum assurance of internal cleanliness.
- Precious metal alloy contact material with gold plating assures excellent high current and dry circuit switching capabilities.

The sensitive 136C Centigrid® relay has a high resistance coil, thus requiring extremely low operating power (200 mW, typical). The advantages of reduced heat dissipation and power supply demands are a plus.

By virtue of its inherently low intercontact capacitance and contact circuit losses, the 136C relay has proven to be an excellent ultraminiature RF switch for frequency ranges well into the UHF spectrum. A typical RF application for the Centigrid® relay is in handheld radio transceivers, wherein the combined features of good RF performance, small size, low coil power dissipation and high reliability make it a preferred method of Transmit- Receive switching (see Figure 1).

The sensitive Series 136C utilizes an internal silicon diode for coil suppression, a Zener diode to protect the MOSFET gate input, and an N-channel enhancement-mode MOSFET chip that enables direct relay interfacing with most microprocessor and IC logic families (CMOS, TTL and MOS).

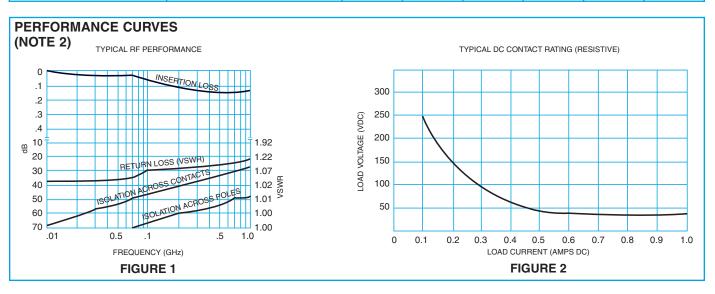
ENVIRONMENTAL AND PHYSICAL SPECIFICATIONS **Temperature** -65°C to +125°C (Ambient) Vibration 30 g's to 3000 Hz (General Note 1) 75 q's, (General Note 1) 6 msec, half-sine **Acceleration** 50 g's **Enclosure** Hermetically sealed Weiaht 0.18 oz. (5.11g) max.

SERIES 136C GENERAL ELECTRICAL SPECIFICATIONS (-65°C to +125°C unless otherwise noted) (Notes 2 & 3)

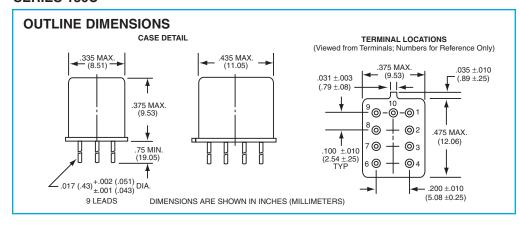
Contact Arrangeme	ent	2 Form C (DPDT)					
Rated Duty		Continuous					
Contact Resistance	е	0.1 ohm max. before life; 0.2 ohm max. after life at 1A/28Vdc (measured 1/8" from header)					
Contact Load Ratin (See Fig. 2 for other resistive voltage/cur	·ĎC`	Resistive: 1 Amp/28Vdc Inductive: 200 mA/28Vdc (320 mH) Lamp: 100 mA/28Vdc Low Level: 10 to 50 µA/10 to 50mV					
Contact Load Ratin	ngs (AC)	Resistive: 250 mA/115Vac, 60 and 400 Hz (Case not grounded) 100 mA/115Vac, 60 and 400 Hz (Case grounded)					
Contact Life Rating	gs	10,000,000 cycles (typical) at low level 1,000,000 cycles (typical) at 0.5A/28Vdc resistive 100,000 cycles min. at all other loads specified above					
Contact Overload I	Rating	2A/28Vdc Resistive (100 cycles min.)					
Contact Carry Rating		Contact factory					
Operate Time		4.0 msec max. at nominal rated coil voltage					
Release Time		7.5 msec max.					
Contact Bounce		1.5 msec max.					
Intercontact Capacitance		0.4 pf typical					
Insulation Resistance		10,000 megohms min. between mutually isolated terminals					
Dielectric Strength		Atmospheric	pressure: 500 Vrms/60Hz	70,000 ft.: 125 Vrms/60Hz			
Negative Coil Transient (Vdc)				1.0 max			
Diode P.I.V. (Vdc)				100 min.			
Zener Voltage (Vdc)				17 min. to 23 max.			
Zener Leakage Current (µA @ 15		.2 Vdc)		2.5 max			
Power FET Characteristics –65°C to +125°C	Gate Voltage to Turn Off (Vdc, Max.)		dc, Max.)	0.5			
	Gate Voltage	to Turn On (Vo	dc, Max.)	3.8 (Note 4)			
	Drain-Source	e Voltage (Vdc,	Max.)	55			

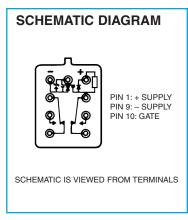
DETAILED ELECTRICAL SPECIFICATIONS (-65°C to +125°C unless otherwise noted) (Note 3)

BASE PART NUMBERS (See Note 8 for full P/N example)			136C-6	136C-9	136C-12	136C-18	136C-26
Coil Voltage (Vdc)	Nom.	5.0	6.0	9.0	12.0	18.0	26.5
	Max.	5.6	8.0	12.0	16.0	24.0	32.0
Coil Current (mAdc @25°C)	Max.	56.0	33.0	26.4	17.7	13.8	10.2
	Min.	43.0	27.0	17.8	11.3	8.4	5.8
Nominal Coil Operating Power @ 25°C (Milliwatts)		250	180	203	180	203	219
Pick-up Voltage (Vdc) (Note 4)	Max.	4.0	4.9	7.3	9.8	14.6	19.5
Drop-out Voltage (Vdc) (Note 4)	Min.	0.13	0.18	0.27	0.36	0.54	0.72
	Max.	2.3	3.2	4.9	6.5	9.8	13.0



SERIES 136C

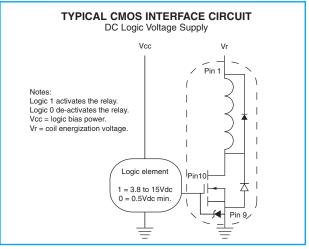




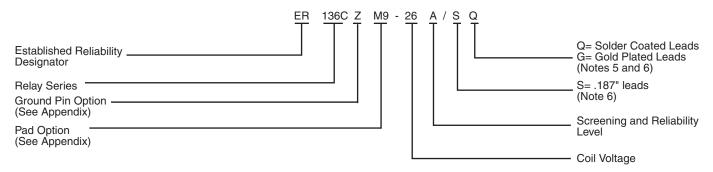
GENERAL NOTES

- Relay contacts will exhibit no chatter in excess of 10 μsec or transfer in excess of 1 μsec.
- 2. "Typical" characteristics are based on available data and are best estimates. No on-going verification tests are performed.
- 3. Unless otherwise specified, parameters are initial values.
- 4. Maximum rated gate voltage = 15 Vdc.
- Unless otherwise specified, relays will be supplied with either gold plated or solder coated leads.
- 6. The slash and character appearing after the slash are not marked on the relay.
- 7. Screened HI-REL versions available. Contact factory.

8.



Teledyne Part Numbering System for $T^2R^{\textcircled{R}}$ Established Reliability Relay



Teledyne Part Numbering System for Military Qualified (JAN) Relays

